# 74HC4094; 74HCT4094 8-stage shift-and-store bus register Rev. 7 — 10 February 2016

Product data sheet

# **General description**

The 74HC4094; 74HCT4094 is an 8-bit serial-in/serial or parallel-out shift register with a storage register and 3-state outputs. Both the shift and storage register have separate clocks. The device features a serial input (D) and two serial outputs (QS1 and QS2) to enable cascading. Data is shifted on the LOW-to-HIGH transitions of the CP input. Data is available at QS1 on the LOW-to-HIGH transitions of the CP input to allow cascading when clock edges are fast. The same data is available at QS2 on the next HIGH-to-LOW transition of the CP input to allow cascading when clock edges are slow. The data in the shift register is transferred to the storage register when the STR input is HIGH. Data in the storage register appears at the outputs whenever the output enable input (OE) is HIGH. A LOW on OE causes the outputs to assume a high-impedance OFF-state. Operation of the OE input does not affect the state of the registers. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

## Features and benefits

- Complies with JEDEC standard JESD7A
- Input levels:
  - ◆ For 74HC4094: CMOS level
  - For 74HCT4094: TTL level
- Low-power dissipation
- ESD protection:
  - HBM JESD22-A114F exceeds 2 000 V
  - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

# **Applications**

- Serial-to-parallel data conversion
- Remote control holding register

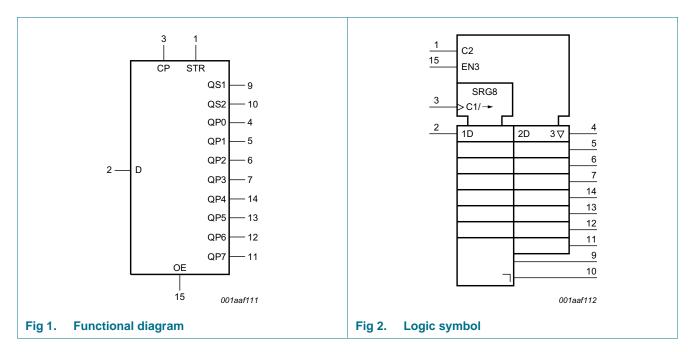


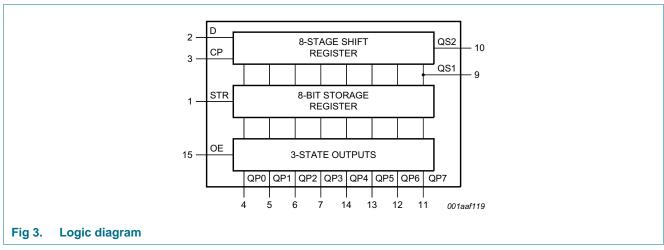
# 4. Ordering information

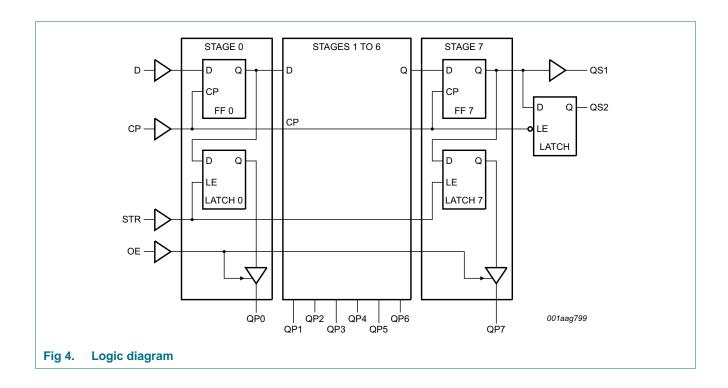
Table 1. Ordering information

Type number	Package	Package										
	Temperature range	Name	Description	Version								
74HC4094D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width	SOT109-1								
74HCT4094D			3.9 mm									
74HC4094DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1								
74HCT4094DB			body width 5.3 mm									
74HC4094PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1								

# 5. Functional diagram



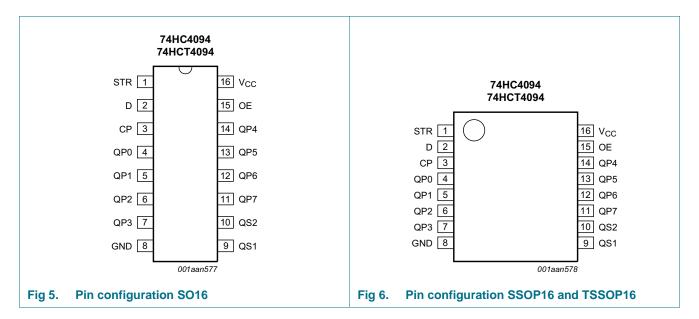




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# 6. Pinning information

# 6.1 Pinning



# 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
STR	1	strobe input
D	2	data input
СР	3	clock input
QP0 to QP7	4, 5, 6, 7, 14, 13, 12, 11	parallel output
V <sub>SS</sub>	8	ground supply voltage
QS1, QS2	9, 10	serial output
OE	15	output enable input
$V_{DD}$	16	supply voltage

# 7. Functional description

Table 3. Function table [1]

Inputs				Parallel o	outputs	Serial out	tputs
СР	OE	STR	D	QP0	QPn	QS1	QS2
$\uparrow$	L	X	Х	Z	Z	Q6S	NC
$\downarrow$	L	X	Х	Z	Z	NC	Q7S
$\uparrow$	Н	L	Х	NC	NC	Q6S	NC
$\uparrow$	Н	Н	L	L	QPn –1	Q6S	NC
<b>↑</b>	Н	Н	Н	Н	QPn –1	Q6S	NC
$\downarrow$	Н	Н	Н	NC	NC	NC	Q7S

[1] At the positive clock edge, the information in the 7th register stage is transferred to the 8th register stage and the QSn outputs.

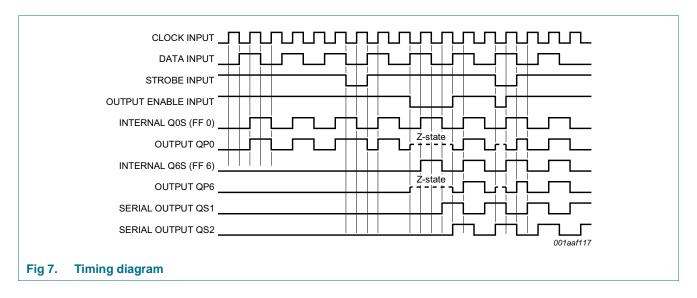
H = HIGH voltage level; L = LOW voltage level; X = don't care;

 $\uparrow$  = positive-going transition;  $\downarrow$  = negative-going transition;

Z = HIGH-impedance OFF-state; NC = no change;

Q6S = the data in register stage 6 before the LOW to HIGH clock transition;

Q7S = the data in register stage 7 before the HIGH to LOW clock transition.



# 8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
lo	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$		-	±25	mA
Icc	supply current			-	+50	mA
I <sub>GND</sub>	ground current			-	-50	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	SO16, SSOP16 and TSSOP16 packages	[1]	-	500	mW

<sup>[1]</sup> For SO16:  $P_{tot}$  derates linearly with 8 mW/K above 70 °C. For SSOP16 and TSSOP16 packages:  $P_{tot}$  derates linearly with 5.5 mW/K above 60 °C.

# 9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	7	4HC409	4	74HCT4094			Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

# 10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC40	94									
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = -20 \mu A$ ; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A$ ; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_O = -20 \mu A$ ; $V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	5.9	-	٧
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	٧
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.5	-	±5.0	-	±10.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-					pF
74HCT4	094				'					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	V

74HC\_HCT4094

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Table 6. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.5	-	±5.0	-	±10	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl <sub>CC</sub>	additional supply current	$\begin{aligned} &V_I = V_{CC} - 2.1 \text{ V;} \\ &\text{other inputs at } V_{CC} \text{ or GND;} \\ &V_{CC} = 4.5 \text{ V to } 5.5 \text{ V;} \\ &I_O = 0 \text{ A} \end{aligned}$								
		per input pin; STR input	-	100	360	-	450	-	490	μΑ
		per input pin; OE input	-	150	540	-	675	-	735	μΑ
		per input pin; CP input	-	150	540	-	675	-	735	μΑ
		per input pin; D input	-	40	144	-	180	-	196	μΑ
Cı	input capacitance		-	3.5	-					pF

# 11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C 1	to +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC40	94									_
t <sub>pd</sub>	propagation	CP to QS1; see Figure 8	1]							
	delay	V <sub>CC</sub> = 2.0 V	-	50	150	-	190	-	225	ns
		V <sub>CC</sub> = 4.5 V	-	18	30	-	38	-	45	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	15	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	14	26	-	33	-	38	ns
		CP to QS2; see Figure 8	1]							
		V <sub>CC</sub> = 2.0 V	-	44	135	-	170	-	205	ns
		V <sub>CC</sub> = 4.5 V	-	16	27	-	34	-	41	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	13	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	13	23	-	29	-	35	ns
		CP to QPn; see Figure 8	1]							
		V <sub>CC</sub> = 2.0 V	-	63	195	-	245	-	295	ns
		V <sub>CC</sub> = 4.5 V	-	23	39	-	49	-	59	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	20	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	18	33	-	42	-	50	ns
		STR to QPn; see Figure 9	1]							
		V <sub>CC</sub> = 2.0 V	-	58	180	-	225	-	270	ns
		V <sub>CC</sub> = 4.5 V	-	21	36	-	45	-	54	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	18	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	17	31	-	38	-	46	ns
t <sub>en</sub>	enable time	OE to QPn; see Figure 11	2]							
		V <sub>CC</sub> = 2.0 V	-	55	175	-	220	-	265	ns
		V <sub>CC</sub> = 4.5 V	-	20	35	-	44	-	53	ns
		V <sub>CC</sub> = 6.0 V	-	16	30	-	37	-	45	ns
t <sub>dis</sub>	disable time	OE to QPn; see Figure 11	3]							
		V <sub>CC</sub> = 2.0 V	-	41	125	-	155	-	190	ns
		V <sub>CC</sub> = 4.5 V	-	15	25	-	31	-	38	ns
		V <sub>CC</sub> = 6.0 V	-	12	21	-	26	-	32	ns
t <sub>t</sub>	transition time	QPn and QSn; see Figure 8	4]							
		V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
		V <sub>CC</sub> = 6.0 V	-	6	13	-	16	-	19	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
t <sub>W</sub>	pulse width	CP HIGH or LOW; see Figure 8								
		V <sub>CC</sub> = 2.0 V	80	14	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	5	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	4	-	17	-	20	-	ns
		STR HIGH; see Figure 9								
		V <sub>CC</sub> = 2.0 V	80	14	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	5	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	4	-	17	-	20	-	ns
t <sub>su</sub>	set-up time	D to CP; see Figure 10								
		V <sub>CC</sub> = 2.0 V	50	14	-	65	-	75	-	ns
		V <sub>CC</sub> = 4.5 V	10	5	-	13	-	15	-	ns
		V <sub>CC</sub> = 6.0 V	9	4	-	11	-	13	-	ns
		CP to STR; see Figure 9								
		V <sub>CC</sub> = 2.0 V	100	28	-	125	-	150	-	ns
		V <sub>CC</sub> = 4.5 V	20	10	-	25	-	30	-	ns
		V <sub>CC</sub> = 6.0 V	17	8	-	21	-	26	-	ns
t <sub>h</sub>	hold time	D to CP; see Figure 10								
		V <sub>CC</sub> = 2.0 V	3	-6	-	3	-	3	-	ns
		V <sub>CC</sub> = 4.5 V	3	-2	-	3	-	3	-	ns
		V <sub>CC</sub> = 6.0 V	3	-2	-	3	-	3	-	ns
		CP to STR; see Figure 9								
		V <sub>CC</sub> = 2.0 V	0	-14	-	0	-	0	-	ns
		V <sub>CC</sub> = 4.5 V	0	-5	-	0	-	0	-	ns
		V <sub>CC</sub> = 6.0 V	0	-4	-	0	-	0	-	ns
f <sub>max</sub>	maximum	CP; see Figure 8								
	frequency	V <sub>CC</sub> = 2.0 V	6.0	28	-	4.8	-	4.0	-	MHz
		V <sub>CC</sub> = 4.5 V	30	87	-	24	-	20	-	MHz
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	95	-	-	-	-	-	MHz
		V <sub>CC</sub> = 6.0 V	35	103	-	28	-	24	-	MHz
C <sub>PD</sub>	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	-	83	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); C<sub>L</sub> = 50 pF unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HCT4	094									1	
t <sub>pd</sub>	propagation	CP to QS1; see Figure 8	[1]								
	delay	V <sub>CC</sub> = 4.5 V		-	23	39	-	49	-	59	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	19	-	-	-	-	-	ns
		CP to QS2; see Figure 8	[1]								
		V <sub>CC</sub> = 4.5 V		-	21	36	-	45	-	54	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	18	-	-	-	-	-	ns
		CP to QPn; see Figure 8	[1]								
		V <sub>CC</sub> = 4.5 V		-	25	43	-	54	-	65	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	21	-	-	-	-	-	ns
		STR to QPn; see Figure 9	[1]								
		V <sub>CC</sub> = 4.5 V		-	22	39	-	49	-	59	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	19	-	-	-	-	-	ns
t <sub>en</sub>	enable time	OE to QPn; see Figure 11	[2]								
		V <sub>CC</sub> = 4.5 V		-	20	35	-	44	-	53	ns
t <sub>dis</sub>	disable time	OE to QPn; see Figure 11	[3]								
		V <sub>CC</sub> = 4.5 V		-	21	35	-	44	-	53	ns
t <sub>t</sub>	transition time	QPn and QSn; see Figure 8	<u>[4]</u>								
		V <sub>CC</sub> = 4.5 V		-	7	15	-	19	-	22	ns
t <sub>W</sub>	pulse width	CP HIGH or LOW; see Figure 8									
		V <sub>CC</sub> = 4.5 V		16	7	-	20	-	24	-	ns
		STR HIGH; see Figure 9									
		V <sub>CC</sub> = 4.5 V		16	5	-	20	-	24	-	ns
t <sub>su</sub>	set-up time	Dn to CP; see Figure 10									
		V <sub>CC</sub> = 4.5 V		10	4	-	13	-	15	-	ns
		CP to STR; see Figure 9									
		V <sub>CC</sub> = 4.5 V		20	9	-	25	-	30	-	ns
t <sub>h</sub>	hold time	Dn to CP; see Figure 10									
		V <sub>CC</sub> = 4.5 V		4	0	-	4	-	4	-	ns
		CP to STR; see Figure 9									
		V <sub>CC</sub> = 4.5 V		0	-4	-	0	-	0	-	ns
f <sub>max</sub>	maximum	CP; see Figure 8									
	frequency	V <sub>CC</sub> = 4.5 V		30	80	-	24	-	20	-	MHz
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF		-	86	-	-	-	-	-	MHz

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	$C_L = 50 \text{ pF; } f = 1 \text{ MHz;}$ V <sub>I</sub> = GND to $V_{CC} - 1.5 \text{ V}$	-	92	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .
- [3]  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .
- [4]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

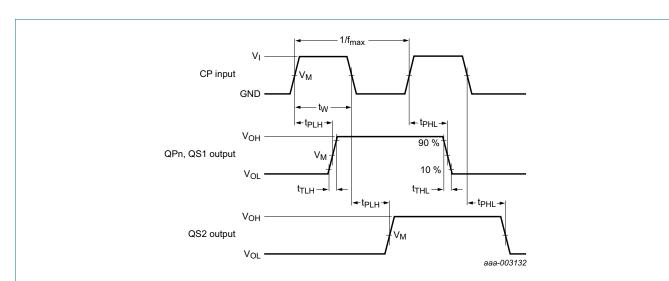
C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$ 

### 12. Waveforms



Measurement points are given in Table 8.

V<sub>OL</sub> and V<sub>OH</sub> are typical voltage output levels that occur with the output load.

Fig 8. Propagation delay input (CP) to output (QPn, QS1, QS2), output transition time, clock input (CP) pulse width and the maximum frequency (CP)

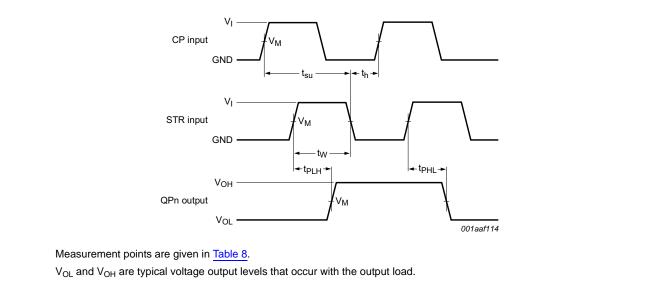
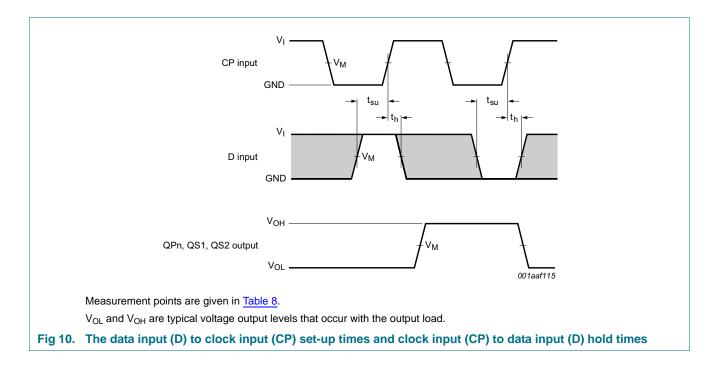


Fig 9. Propagation delay strobe input (STR) to output (QPn), strobe input (STR) pulse width and the clock set-up and hold times for strobe input



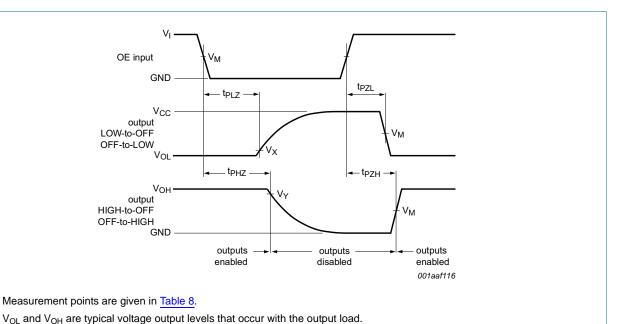
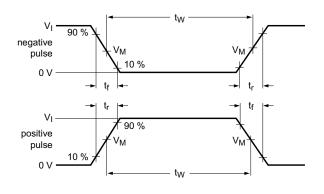
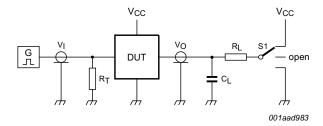


Fig 11. Enable and disable times

Table 8. Measurement points

Туре	Input	Output	Output						
	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>					
74HC4094	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	0.1V <sub>OH</sub>	0.9V <sub>OH</sub>					
74HCT4094	1.3 V	1.3 V	0.1V <sub>OH</sub>	0.9V <sub>OH</sub>					





Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $C_L$  = Load capacitance including jig and probe capacitance.

R<sub>L</sub> = Load resistance.

S1 = Test selection switch.

Fig 12. Test circuit for measuring switching times

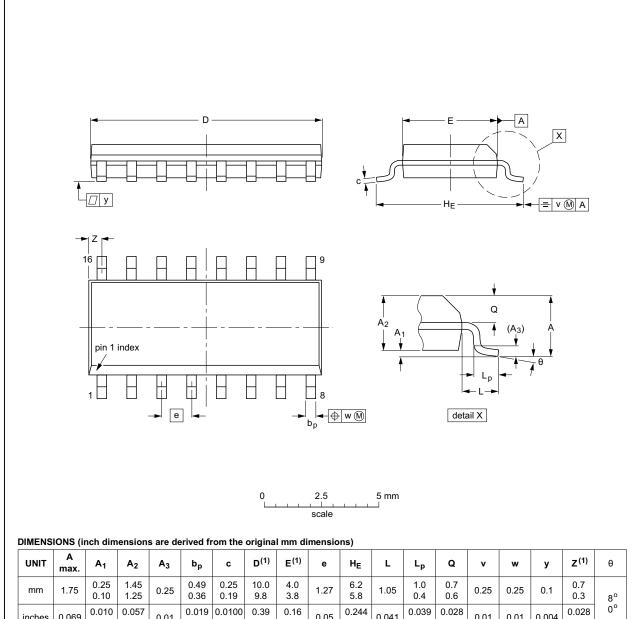
Table 9. Test data

Туре	Input		Load				
	VI	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	R <sub>L</sub>	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
74HC4094	V <sub>CC</sub>	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>
74HCT4094	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>

# 13. Package outline

#### SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	e	HE	٦	Lp	Q	٧	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

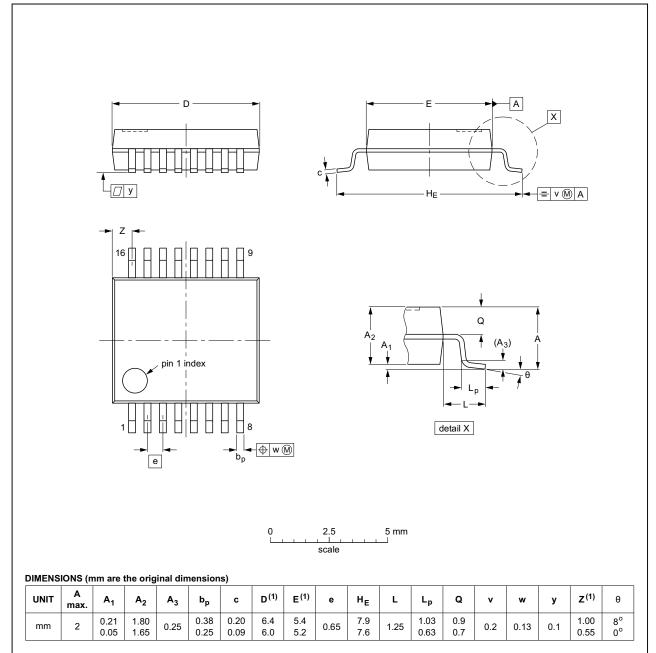
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012				<del>99-12-27</del> 03-02-19

Fig 13. Package outline SOT109-1 (SO16)

#### SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



#### Note

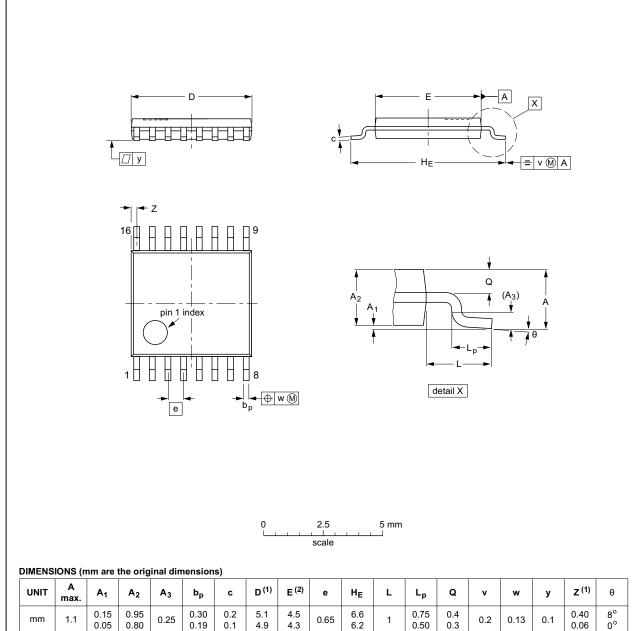
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT338-1		MO-150				<del>99-12-27</del> 03-02-19

Fig 14. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	<b>A</b> <sub>3</sub>	bp	U	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT403-1		MO-153				<del>99-12-27</del> 03-02-18

Fig 15. Package outline SOT403-1 (TSSOP16)

74HC\_HCT4094

# 14. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 15. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4094 v.7	20160210	Product data sheet	-	74HC_HCT4094 v.6
Modifications:	Type numb	ers 74HC4094N and 74H	CT4094N (SOT38-4)	removed.
74HC_HCT4094 v.6	20121231	Product data sheet	-	74HC_HCT4094 v.5
Modifications:	General de	scription updated.		
74HC_HCT4094 v.5	20120628	Product data sheet	-	74HC_HCT4094 v.4
Modifications:	<ul> <li>V<sub>X</sub> and V<sub>Y</sub></li> </ul>	measurement points adde	d to Table 8.	
74HC_HCT4094 v.4	20111219	Product data sheet	-	74HC_HCT4094 v.3
Modifications:	<ul> <li>Legal page</li> </ul>	s updated.		
74HC_HCT4094 v.3	20110214	Product data sheet	-	74HC_HCT4094_CNV v.2
74HC_HCT4094_CNV v.2	19970901	Product specification	-	-

# 16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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# 74HC4094; 74HCT4094

#### 8-stage shift-and-store bus register

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